## AMENDMENTS TO THE SPECIFICATION

**Please substitute the below amended paragraphs for the respective portion of the specification:**

[0015] Figures ~~3 A-E~~ 3A – 3E are cross-sectional views illustrating an array of resistance variable material cells in various stages of construction.

[0023] The process can proceed to form 115 a layer of chalcogenide glass, such as germanium selenide ($Ge_xSe_{1-x}$), on the lower electrode. The process can include forming the layer of chalcogenide glass below a layer of silver selenide, above the layer of silver selenide, or both. It will thus be understood that in some embodiments of the process, the forming 115 of the layer of chalcogenide glass on the lower electrode is optional. Where the layer of chalcogenide glass is formed 115 on the lower electrode, the layer of chalcogenide glass is preferably between about 50 angstroms (Å) to about 1000 (Å) thick. In one embodiment, the layer of chalcogenide glass is about 150 Å thick. An exemplary chalcogenide glass is $Ge_{0.4}Se_{0.6}$.